PROCESS BATCH SHEET (Boron Drive-in/Wet Oxidation) Issue 5 Pg____of____

ENSC Batch No MaterialOrientation Resistivity		_Wafers Started Date Size Thickness Type Vendor Batch #SFU P.O						
				Wafer VendorVend			or Batch #SFU P.O	
				Process Step #	Process Conditions	Oper & Wafer #	Comments	
			Wafers must be put through a full RCA clean, per specs, just before this process. If necessary, use modified process to protect oxide.					
A	Prepare Furnace Dry N2 @ 4 scfh. Ramp temp to 750-800C. Start bubbler.							
B	Load Wafers into Boat Use correct forceps, boat and white elephant							
C	Push Boat into Furnace Dry N2 @ 4 scfh. Temp = 800C. Push @ < 4"/min							
D	Ramp Furnace Up Dry N2 @ 4 scfh. Set operating temp.							
E	Oxidation/Drive-in Wet N2 @ about 4, sufficient for good action in the bubbler. Open valve and start timer. Close valve at end of time.		Desired oxide thickness =microns Time =min Temp =C					
F	Ramp Furnace Down Dry N2 @ 4 scfh. Temp=400C. Bubbler off.							
G	Pull Boat and Unload Pull when all zones < 800C. Max pull < 4"/min							
H	Return Furnace to Idle O2 @ 0. N2 @ 0.5-1.0 scfh							
I	Inspect Visual, etc.							